
Session Title:	50. Oxide TFT I
Date:	Aug. 26, 2016 (Friday)
Time:	08:30~09:50
Room	Room B (Halla B)
Session Chairs	Prof. Shengdong Zhang (Peking Univ., China) Prof. Do Kyung Hwang (KIST, Korea)

B50-1

08:30~08:55

[Invited] Simplicity Meets High Performance: Solution Processed Metal Oxide TFTs

E. Fortunato, R. Branquinho, E. Carlos, P. Barquinhal, D. Salgueiro (Universidade NOVA de Lisboa and CEMOP/UNINOVA, Portugal), A. Liu, F.K. Shan (Qingdao Univ., China), and R. Martins (Universidade NOVA de Lisboa and CEMOP/UNINOVA, Portugal)

B50-2

08:55~09:20

[Invited] Printed and Electrolyte-Gated Oxide Electronics

Subho Dasgupta (Indian Inst. of Science, India)

B50-3

09:20~09:35

Fiber-Based Metal-Oxide Thin-Film Transistors (TFTs) Using Low-Temperature Photoactivation for Electronic Textiles

Jae Sang Heo, Jun Ho Lee, Su Min Jung (Chung-Ang Univ., Korea), Han Lim Kang (Korea Univ., Korea), and Sung Kyu Park (Chung-Ang Univ., Korea)

B50-4

09:35~09:50

Copper Top Gate Oxide TFT with Double-Layered SiNx/Al₂O₃ Gate Insulator for the Application to the Large Area, High Resolution AMOLED

Yujin Kim, Geumbi Moon, Kyoungwoo Park, and Sang-Hee Ko Park (KAIST, Korea)